# Onsemi

# FFSH40120ADN-F155

#### Description

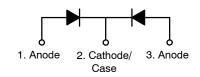
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

#### Features

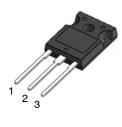
- Max Junction Temperature 175°C
- Avalanche Rated 200 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb-Free, Halogen Free/BFR Free and RoHS Compliant

#### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

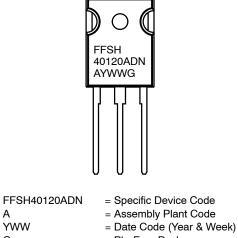


Schottky Diode



TO-247-3LD CASE 340CH

#### MARKING DIAGRAM



= Pb-Free Package

#### **ORDERING INFORMATION**

Α YWW

G

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSH40120ADN-F155

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		1200	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		200	mJ
١ <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 148°C		20* / 40**	А
I <sub>F,Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	1190	А
		T <sub>C</sub> = 150°C, 10 μs	990	А
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	135	А
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	74	А
P <sub>TOT</sub>	Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	220	W
		T <sub>C</sub> = 150°C	37	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		–55 to +175	°C
	TO-247 Mounting Torque, M3 Screw	60	Ncm	

#### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted) (per leg)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: \* Per leg, \*\* Per Device.

1.  $E_{AS}$  of 200 mJ is based on starting  $T_J$  = 25°C, L = 0.5 mH,  $I_{AS}$  = 29 A, V = 150 V.

#### **THERMAL CHARACTERISTICS**

Symbol	Parameter	Value	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max	0.68* / 0.34**	°C/W

NOTE: \* Per leg, \*\* Per Device.

#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted) (per leg)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	$I_{F} = 20 \text{ A}, T_{C} = 25^{\circ}\text{C}$	-	1.45	1.75	V
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 125°C	-	1.7	2.0	
		I <sub>F</sub> = 20 A, T <sub>C</sub> = 175°C	-	2.0	2.4	
I <sub>R</sub>	Reverse Current	$V_{\rm R}$ = 1200 V, $T_{\rm C}$ = 25°C	-	-	200	μΑ
		$V_{\rm R}$ = 1200 V, $T_{\rm C}$ = 125°C	-	-	300	
		$V_{\rm R}$ = 1200 V, $T_{\rm C}$ = 175°C	-	-	400	
Q <sub>C</sub>	Total Capacitive Charge	V = 800 V	-	120	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	1220	-	pF
		V <sub>R</sub> = 400 V, f = 100 kHz	-	111	-	
		V <sub>R</sub> = 800 V, f = 100 kHz	_	88	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

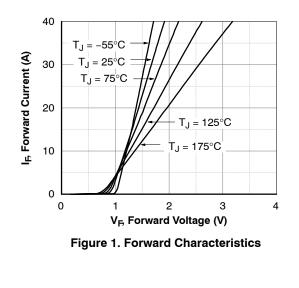
#### **ORDERING INFORMATION**

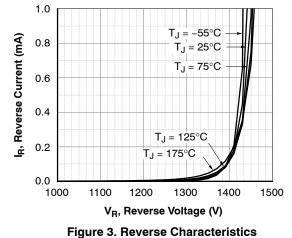
Part Number	Top Marking	Package	Packing Method	Quantity
FFSH40120ADN-F155	FFSH40120ADN	TO-247-3LD	Tube	30 Units

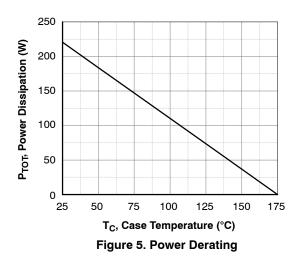
# FFSH40120ADN-F155

### **TYPICAL CHARACTERISTICS**

 $(T_J = 25^{\circ}C \text{ UNLESS OTHERWISE NOTED (PER LEG)})$ 







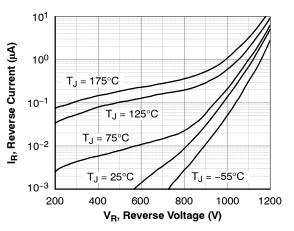
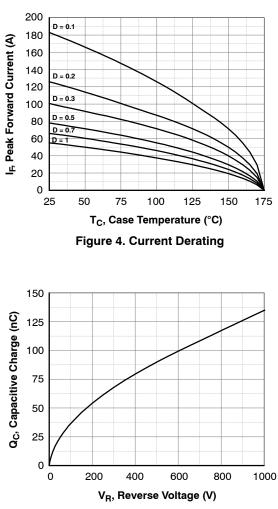


Figure 2. Reverse Characteristics





## FFSH40120ADN-F155

 $\label{eq:typical characteristics} \begin{array}{l} \textbf{Typical characteristics} \ (\texttt{CONTINUED}) \\ \textbf{(} \textbf{T}_{\text{J}} = 25^{\circ}\texttt{C} \ \textbf{UNLESS} \ \textbf{OTHERWISE} \ \textbf{NOTED} \ \textbf{(PER LEG))} \end{array}$ 

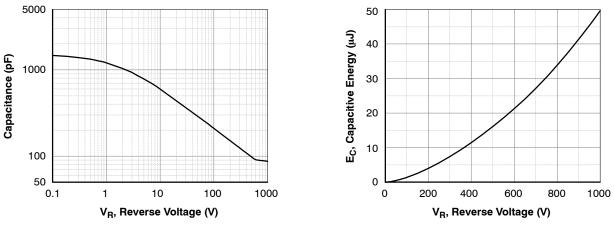
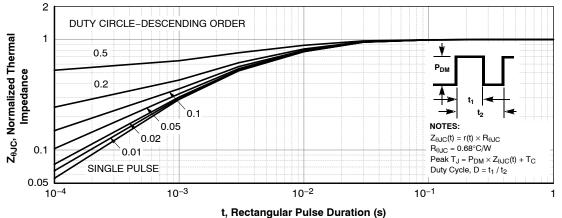


Figure 7. Capacitance vs. Reverse Voltage

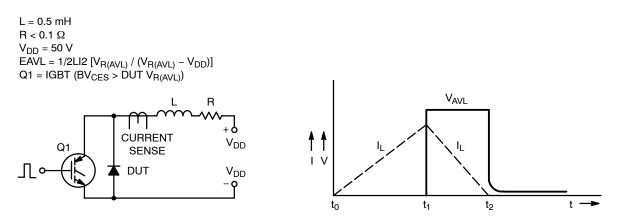


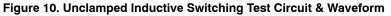


t, nectaligular Pulse Duration (s)

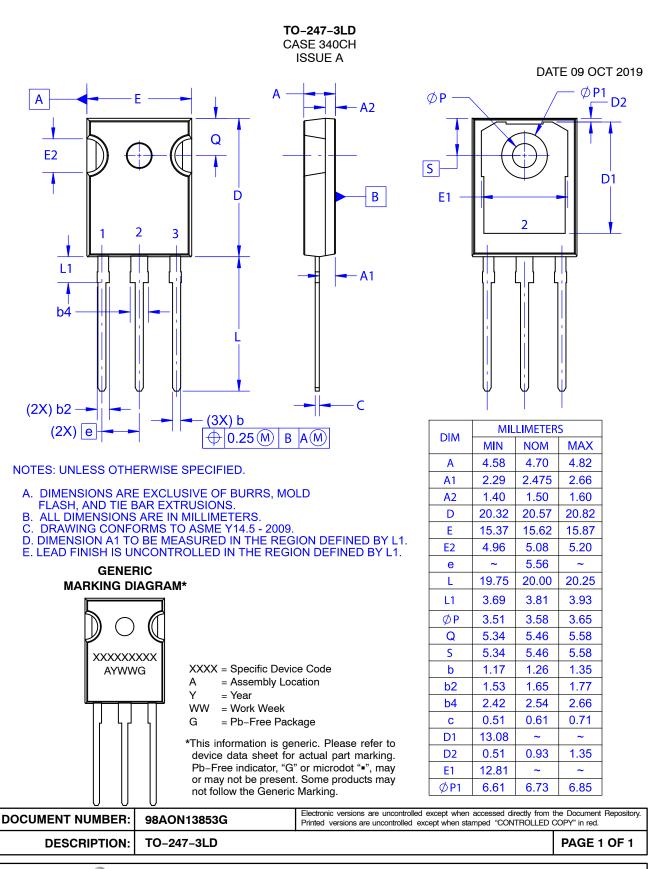
Figure 9. Junction-to-Case Transient Thermal Response Curve

#### **TEST CIRCUIT AND WAVEFORMS**









ON Semiconductor and use trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent\_Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or indental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification. Buyer shall indemnify and hold onsemi and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs,

#### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: <u>www.onsemi.com/support</u> For additional information, please contact your local Sales Representative at <u>www.onsemi.com/support/sales</u>